

## Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <http://www.nxp.com>, <http://www.philips.com/> or <http://www.semiconductors.philips.com/>, use **<http://www.nexperia.com>**

Instead of [sales.addresses@www.nxp.com](mailto:sales.addresses@www.nxp.com) or [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com), use **[salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © **Nexperia B.V. (year). All rights reserved.**

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **[salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia



# BSS84

## P-channel enhancement mode vertical DMOS transistor

Rev. 06 — 16 December 2008

Product data sheet

## 1. Product profile

### 1.1 General description

P-channel enhancement mode vertical Diffusion Metal-Oxide Semiconductor (DMOS) transistor in a small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

| Type number <sup>[1]</sup> | Package |          |
|----------------------------|---------|----------|
|                            | NXP     | JEDEC    |
| BSS84                      | SOT23   | TO-236AB |
| BSS84/DG                   |         |          |

[1] /DG: halogen-free

### 1.2 Features

- Low threshold voltage
- High-speed switching
- Direct interface to CMOS and Transistor-Transistor Logic (TTL)
- No secondary breakdown

### 1.3 Applications

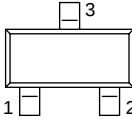
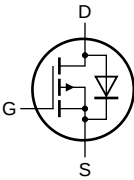
- Line current interrupter in telephone sets
- Relay, high-speed and line transformer drivers

### 1.4 Quick reference data

- $V_{DS} \leq -50 \text{ V}$
- $I_D \leq -130 \text{ mA}$
- $R_{DS(on)} \leq 10 \text{ } \Omega$
- $P_{tot} \leq 250 \text{ mW}$

2. Pinning information

Table 2. Pinning

| Pin | Symbol | Description | Simplified outline                                                                                      | Graphic symbol                                                                                   |
|-----|--------|-------------|---------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------|
| 1   | G      | gate        | <br>SOT23 (TO-236AB) | <br>001aaa025 |
| 2   | S      | source      |                                                                                                         |                                                                                                  |
| 3   | D      | drain       |                                                                                                         |                                                                                                  |

3. Ordering information

Table 3. Ordering information

| Type number <sup>[1]</sup> | Package  |                                          |         |
|----------------------------|----------|------------------------------------------|---------|
|                            | Name     | Description                              | Version |
| BSS84                      | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |
| BSS84/DG                   |          |                                          |         |

[1] /DG: halogen-free

4. Marking

Table 4. Marking codes

| Type number <sup>[1]</sup> | Marking code <sup>[2]</sup> |
|----------------------------|-----------------------------|
| BSS84                      | 13*                         |
| BSS84/DG                   | ZV*                         |

[1] /DG: halogen-free

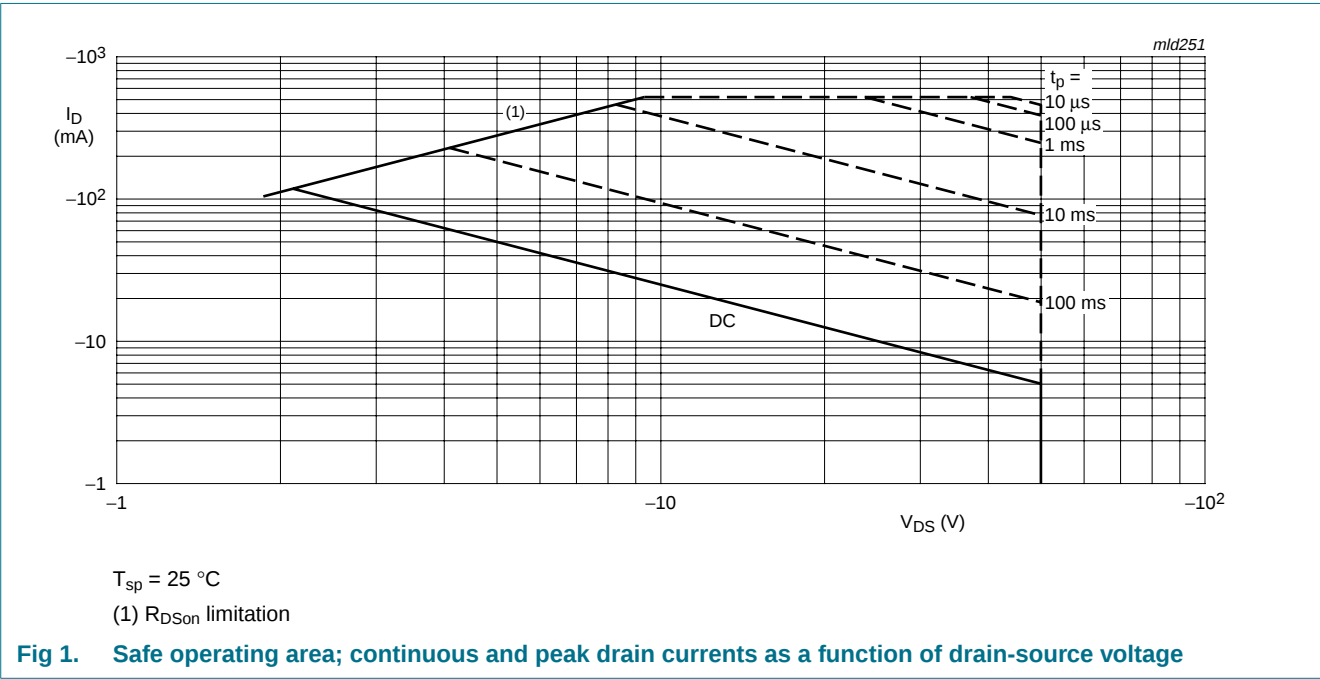
[2] \* = -: made in Hong Kong  
\* = p: made in Hong Kong  
\* = t: made in Malaysia  
\* = W: made in China

5. Limiting values

Table 5. Limiting values  
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions                                                                                             | Min | Max      | Unit               |
|-----------|-------------------------|--------------------------------------------------------------------------------------------------------|-----|----------|--------------------|
| $V_{DS}$  | drain-source voltage    | $25\text{ }^{\circ}\text{C} \leq T_j \leq 150\text{ }^{\circ}\text{C}$                                 | -   | -50      | V                  |
| $V_{GS}$  | gate-source voltage     |                                                                                                        | -   | $\pm 20$ | V                  |
| $I_D$     | drain current           | $T_{sp} = 25\text{ }^{\circ}\text{C}; V_{GS} = -10\text{ V};$<br>see <a href="#">Figure 1</a>          | -   | -130     | mA                 |
|           |                         | $T_{sp} = 100\text{ }^{\circ}\text{C};$<br>$V_{GS} = -10\text{ V}$                                     | -   | -75      | mA                 |
| $I_{DM}$  | peak drain current      | $T_{sp} = 25\text{ }^{\circ}\text{C}; t_p \leq 10\text{ }\mu\text{s};$<br>see <a href="#">Figure 1</a> | -   | -520     | mA                 |
| $P_{tot}$ | total power dissipation | $T_{sp} = 25\text{ }^{\circ}\text{C};$ see <a href="#">Figure 2</a> <sup>[1]</sup>                     | -   | 250      | mW                 |
| $T_{stg}$ | storage temperature     |                                                                                                        | -65 | +150     | $^{\circ}\text{C}$ |
| $T_j$     | junction temperature    |                                                                                                        | -65 | +150     | $^{\circ}\text{C}$ |

[1] Device mounted on a Printed-Circuit Board (PCB).



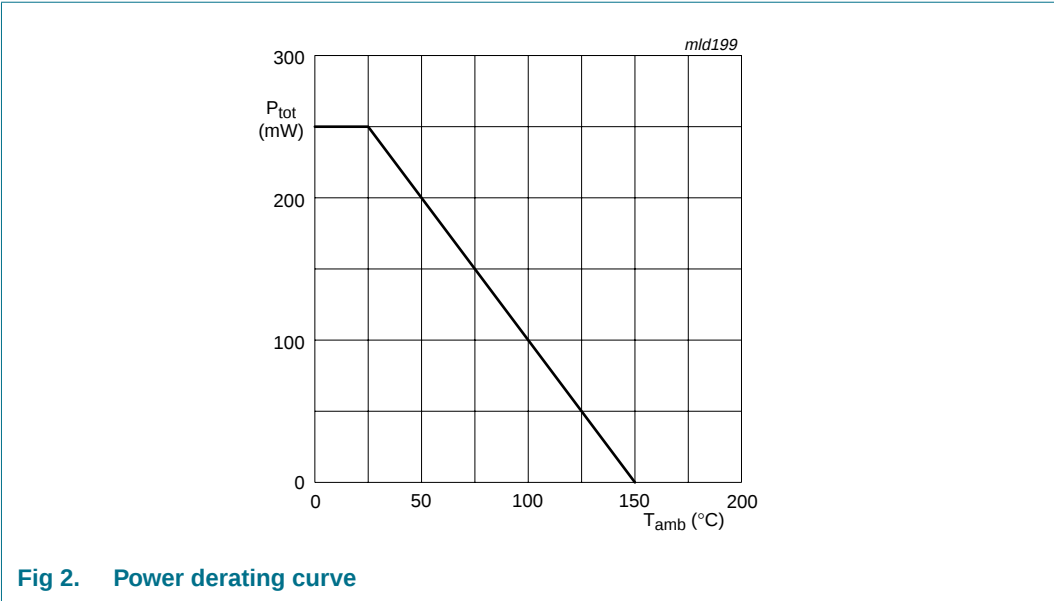


Fig 2. Power derating curve

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol        | Parameter                                   | Conditions                   | Min | Typ | Max | Unit |
|---------------|---------------------------------------------|------------------------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | see <a href="#">Figure 3</a> | [1] | -   | 500 | K/W  |

[1] Mounted on a PCB, vertical in still air.

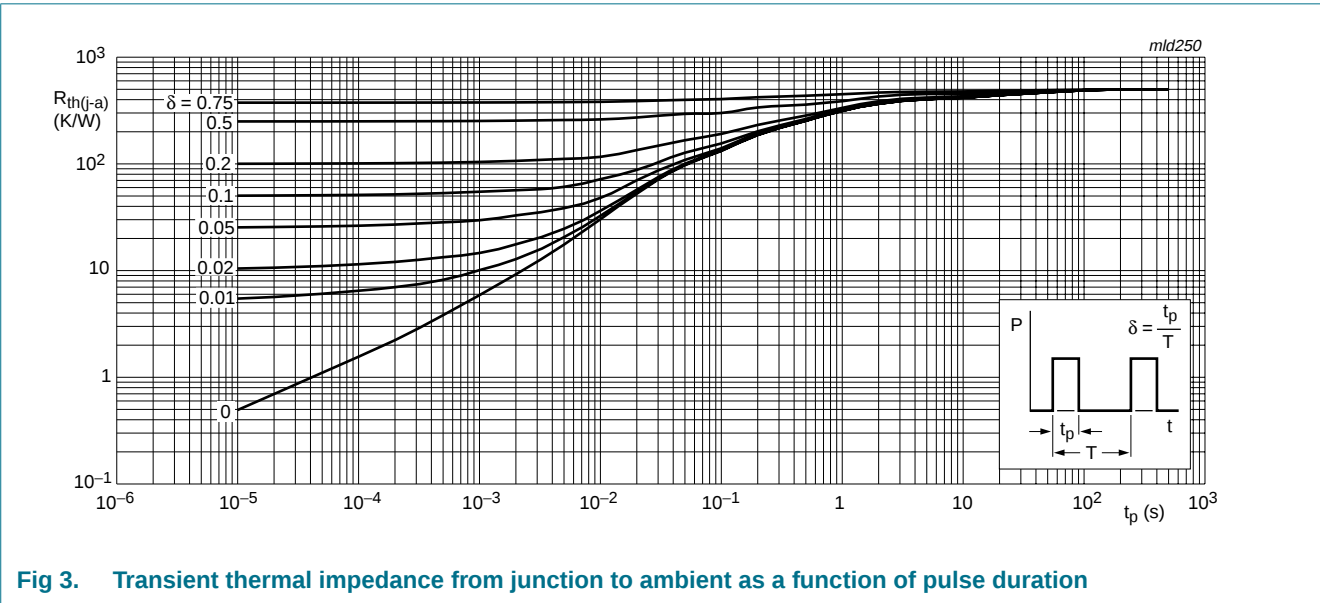


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration

## 7. Characteristics

**Table 7. Characteristics**

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

| Symbol                         | Parameter                        | Conditions                                                                                                                                                 | Min  | Typ | Max  | Unit          |
|--------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-----|------|---------------|
| <b>Static characteristics</b>  |                                  |                                                                                                                                                            |      |     |      |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = -10\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$                                                                                                     | -50  | -   | -    | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage    | $I_D = -1\text{ mA}$ ; $V_{DS} = V_{GS}$ ;<br>see <a href="#">Figure 8</a>                                                                                 |      |     |      |               |
|                                |                                  | $T_j = 25\text{ }^{\circ}\text{C}$                                                                                                                         | -0.8 | -   | -2   | V             |
|                                |                                  | $T_j = -55\text{ }^{\circ}\text{C}$                                                                                                                        | -    | -   | -1.8 | V             |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = -40\text{ V}$ ; $V_{GS} = 0\text{ V}$                                                                                                            |      |     |      |               |
|                                |                                  | $T_j = 25\text{ }^{\circ}\text{C}$                                                                                                                         | -    | -   | -100 | nA            |
|                                |                                  | $V_{DS} = -50\text{ V}$ ; $V_{GS} = 0\text{ V}$                                                                                                            |      |     |      |               |
|                                |                                  | $T_j = 25\text{ }^{\circ}\text{C}$                                                                                                                         | -    | -   | -10  | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = +20\text{ V}$ ; $V_{DS} = 0\text{ V}$                                                                                                            | -    | -   | 100  | nA            |
|                                |                                  | $V_{GS} = -20\text{ V}$ ; $V_{DS} = 0\text{ V}$                                                                                                            | -    | -   | 100  | nA            |
|                                |                                  | $T_j = 125\text{ }^{\circ}\text{C}$                                                                                                                        | -    | -   | -60  | $\mu\text{A}$ |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = -10\text{ V}$ ;<br>$I_D = -130\text{ mA}$ ;<br>see <a href="#">Figure 5</a> and <a href="#">7</a>                                                | -    | 6   | 10   | $\Omega$      |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                                                            |      |     |      |               |
| $ Y_{fs} $                     | transfer admittance              | $V_{DS} = -25\text{ V}$ ;<br>$I_D = -130\text{ mA}$                                                                                                        | 50   | -   | -    | mS            |
| $C_{iss}$                      | input capacitance                | $V_{GS} = 0\text{ V}$ ; $V_{DS} = -25\text{ V}$ ;<br>$f = 1\text{ MHz}$ ; see <a href="#">Figure 9</a>                                                     | -    | 25  | 45   | pF            |
| $C_{oss}$                      | output capacitance               |                                                                                                                                                            | -    | 15  | 25   | pF            |
| $C_{rss}$                      | reverse transfer capacitance     |                                                                                                                                                            | -    | 3.5 | 12   | pF            |
| $t_{on}$                       | turn-on time                     | $V_{DS} = -40\text{ V}$ ; $V_{GS} = 0\text{ V}$<br>to $-10\text{ V}$ ; $I_D = -200\text{ mA}$ ;<br>see <a href="#">Figure 10</a> and <a href="#">11</a>    | -    | 3   | -    | ns            |
| $t_{off}$                      | turn-off time                    | $V_{DS} = -40\text{ V}$ ;<br>$V_{GS} = -10\text{ V}$ to $0\text{ V}$ ;<br>$I_D = -200\text{ mA}$ ;<br>see <a href="#">Figure 10</a> and <a href="#">11</a> | -    | 7   | -    | ns            |

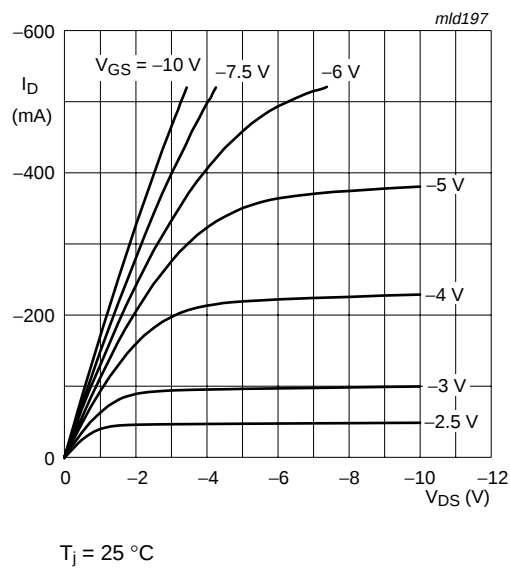


Fig 4. Output characteristics: drain current as a function of drain-source voltage; typical values

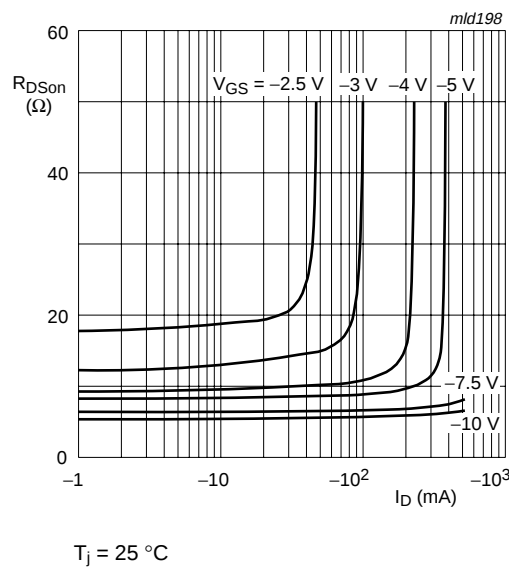


Fig 5. Drain-source on-state resistance as a function of drain current; typical values

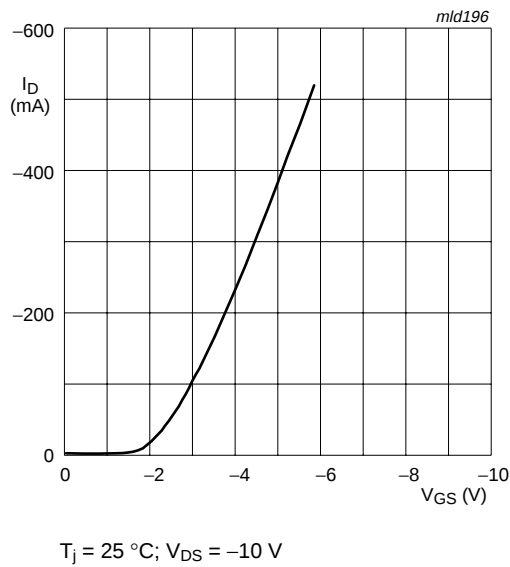


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

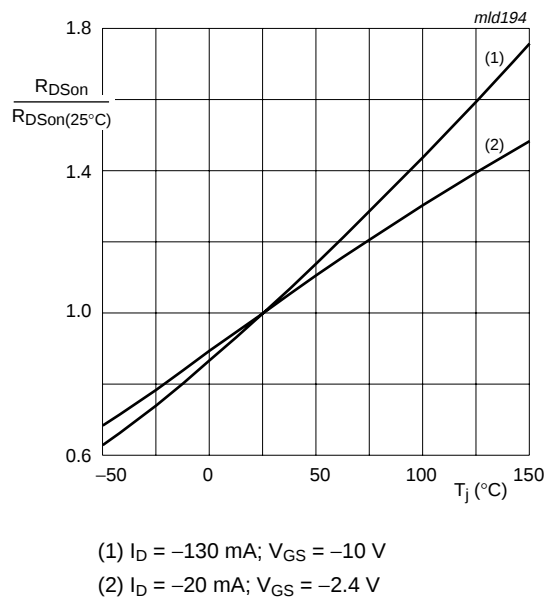
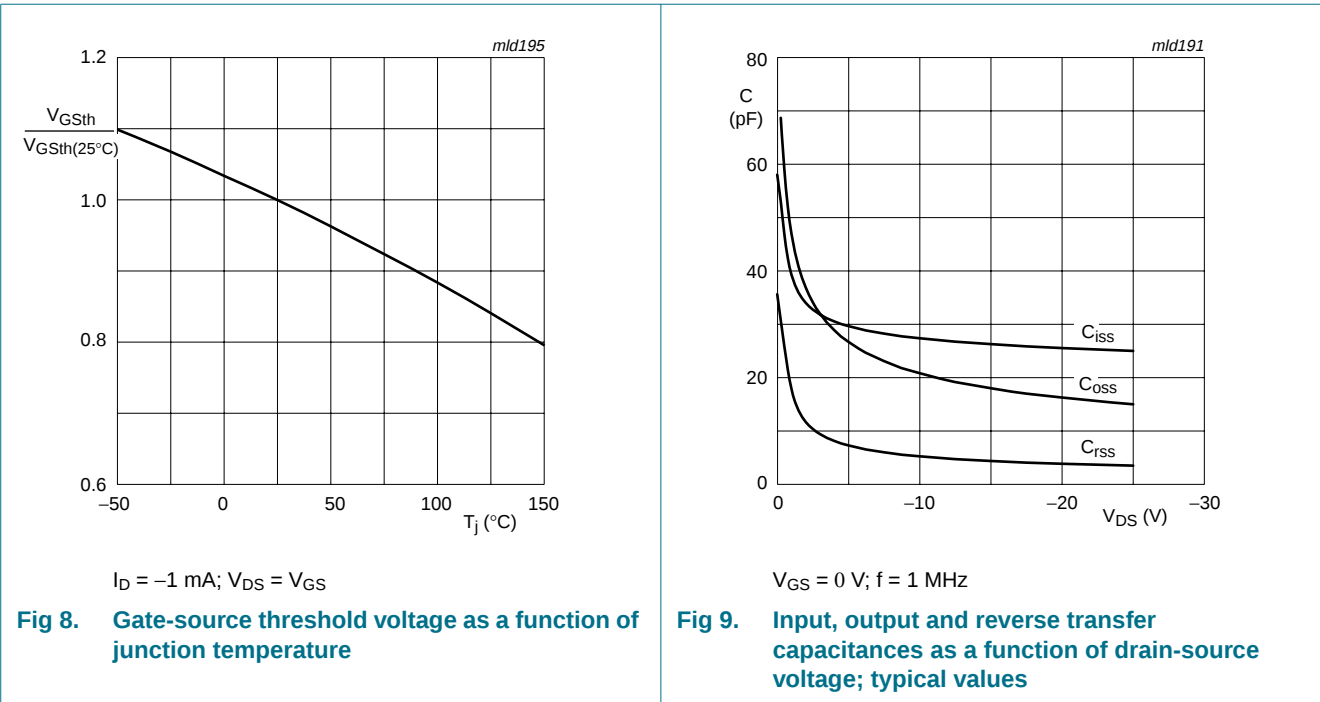
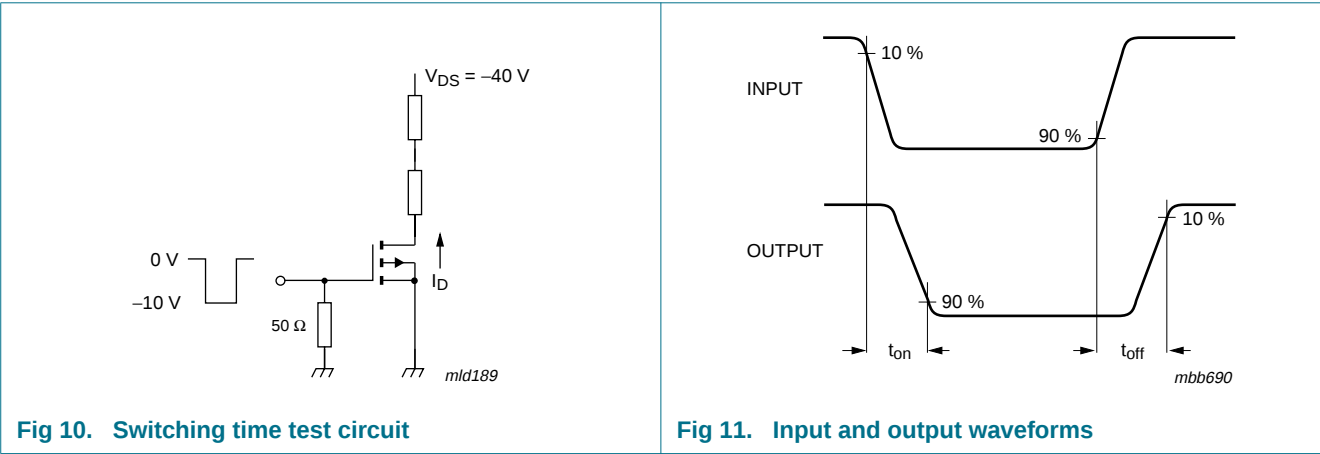


Fig 7. Normalized drain-source on-state resistance factor as a function of junction temperature



8. Test information





## 10. Revision history

Table 8. Revision history

| Document ID    | Release date                                                                     | Data sheet status     | Change notice | Supersedes |
|----------------|----------------------------------------------------------------------------------|-----------------------|---------------|------------|
| BSS84_6        | 20081216                                                                         | Product data sheet    | -             | BSS84_5    |
| Modifications: | • <a href="#">Table 5 "Limiting values"</a> : $P_{tot}$ figure reference updated |                       |               |            |
| BSS84_5        | 20081209                                                                         | Product data sheet    | -             | BSS84_4    |
| BSS84_4        | 20070717                                                                         | Product data sheet    | -             | BSS84_3    |
| BSS84_3        | 20030804                                                                         | Product specification | -             | BSS84_2    |
| BSS84_2        | 19970618                                                                         | Product specification | -             | BSS84_1    |
| BSS84_1        | 19950407                                                                         | Product specification | -             | -          |

## 11. Legal information

### 11.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition                                                                            |
|-----------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 11.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

### 11.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Terms and conditions of sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

### 11.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 12. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

13. Contents

1 Product profile ..... 1

1.1 General description..... 1

1.2 Features ..... 1

1.3 Applications ..... 1

1.4 Quick reference data..... 1

2 Pinning information..... 2

3 Ordering information..... 2

4 Marking..... 2

5 Limiting values..... 3

6 Thermal characteristics..... 4

7 Characteristics..... 5

8 Test information..... 7

9 Package outline ..... 8

10 Revision history..... 9

11 Legal information..... 10

11.1 Data sheet status ..... 10

11.2 Definitions..... 10

11.3 Disclaimers..... 10

11.4 Trademarks..... 10

12 Contact information..... 10

13 Contents ..... 11



Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.